

As a below named inventor, I hereby declare that:

My residence, post office address and citizenship are as stated below next to my name,

I believe I am the original, first and sole inventor (if only one name is listed below) or an original, first and joint inventor (if plural names are listed below) of the subject matter which is claimed and for which a patent is sought on the invention entitled:

METHOD OF FORMING DIFFERENT OXIDE THICKNESS FOR HIGH VOLTAGE TRANSISTOR AND MEMORY CELL TUNNEL DIELECTRIC

		ed on (if	applicable).
	ve reviewed and understand s amended by any amendm	d the contents of the above-identified the terred to above.	d specification,
I acknowledge the duty 1.56.	to disclose all information	n which is material to patentability a	as defined in 37 CFR §
application(s) for pater designated at least one	nt or inventor's certificate, of country other than the Unit of for patent or inventor's ce	U.S.C. § 119(a)-(d) or § 365(b) of a or § 365(a) of any PCT Internationa ted States, listed below and have al rtificate having a filing date before	l application which so identified below
Prior Foreign Applicat	ion(s)		Priority Claimed Yes No
Number	Country	Day/Month/Year Filed	
Number	Country	Day/Month/Year Filed	
I hereby claim the bend	efit under 35 U.S.C. § 119((e) of any United States provisional	application(s) below.
Application Number	Filing Date		
Application Number	Filing Date		

I hereby claim the benefit under 35 U.S.C. § 120 of any United States application(s), or § 365(c) of any PCT International application designating the United States, listed below and, insofar as the subject matter of each of the claims of this application is not disclosed in the prior United States application in the manner provided by the first paragraph of 35 U.S.C. § 112, I acknowledge the duty to disclose all information

Application Number	Filing Date	Status: Patented, Pending, Abandoned
Application Number	Filing Date	Status: Patented, Pending, Abandoned
on information and belief knowledge that willful fals	are believed to be true se statements and the 001 and that such will	of my own knowledge are true and that all statements in e; and further that these statements were made with the like so made are punishable by fine or imprisonment or ful false statements may jeopardize the validity of the
Full name of sole or first i	nventorGe	eeng-Chuan Chern
Inventor's signature		Date
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		ana Lee
Inventor's signature		
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